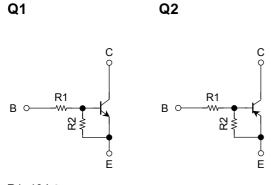
TOSHIBA Transistor Silicon NPN · PNP Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

# **RN4962FE**

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

- Two devices are incorporated into an Extreme-Super-Mini (6 pin) • package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.

#### **Equivalent Circuit and Bias Resistor Values**



R1: 10 kΩ

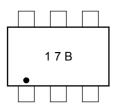
R2: 10 kΩ

(Q1, Q2 common)

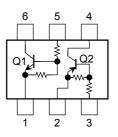
#### 1.6±0.05 1.2±0.05 6 0.5 1.0±0.05 I.6±0.05 0.2±0.05 5 2 0.5 30 0.55±0.0 0.12±0.05 1. EMITTER 1 (E1) 2. EMITTER 2 3. BASE 2 4. COLLECTOR 2 (E2) (B2) (C2) (B1) 5. BASE 1 6. COLLECTOR 1 (CI) ES6 JEDEC JEITA \_\_\_\_ TOSHIBA \_

Weight: g (typ.)

#### Marking



#### **Equivalent Circuit (top view)**



Unit: mm

# Maximum Ratings (Ta = 25°C) (Q1)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	10	V
Collector current	Ι <sub>C</sub>	100	mA

### Maximum Ratings (Ta = 25°C) (Q2)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-10	V
Collector current	۱ <sub>С</sub>	-100	mA

#### Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit
Collector power dissipation	P <sub>C</sub> (Note)	100	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note: Total rating

# Electrical Characteristics (Ta = 25°C) (Q1)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB}=50~V,~I_{E}=0$	_	_	100	nA
	ICEO	$V_{CE}=50~V,~I_B=0$	_		500	
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 10 \text{ V}, I_{C} = 0$	0.38	_	0.71	mA
DC current gain	h <sub>FE</sub>	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 10 \text{ mA}$	50	_	_	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_{C} = 5 \text{ mA}, I_{B} = 0.25 \text{ mA}$	_	0.1	0.3	V
Input voltage (ON)	V <sub>I (ON)</sub>	$V_{CE} = 0.2 \text{ V}, I_{C} = 5 \text{ mA}$	1.2	_	2.4	V
Input voltage (OFF)	VI (OFF)	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 0.1 \text{ mA}$	1.0	_	1.5	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 50 \text{ V}, I_{C} = 0$	_	250	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 50 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$		3	6	pF

### **Electrical Characteristics (Ta = 25°C) (Q2)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB}=-50~V,~I_{E}=0$		_	-100	nA
	ICEO	$V_{CE}=-50~V,~I_B=0$	_	_	-500	
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = -10 \text{ V}, I_C = 0$	-0.38	_	-0.71	mA
DC current gain	h <sub>FE</sub>	$V_{CE} = -5 \text{ V}, \text{ I}_{C} = -10 \text{ mA}$	50	_	_	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_{C} = -5 \text{ mA}, I_{B} = -0.25 \text{ mA}$		-0.1	-0.3	V
Input voltage (ON)	V <sub>I (ON)</sub>	$V_{CE} = -0.2$ V, $I_C = -5$ mA	-1.2	_	-2.4	V
Input voltage (OFF)	V <sub>I (OFF)</sub>	$V_{CE} = -5 \text{ V}, \text{ I}_{C} = -0.1 \text{ mA}$	-1.0	_	-1.5	V
Transition frequency	f <sub>T</sub>	$V_{CE} = -50 \text{ V}, \text{ I}_{C} = 0$		200	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$		3	6	pF

### Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input resistor	R1	—	7	10	13	kΩ
Resistor ratio	R1/R2		0.9	1.0	1.1	

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